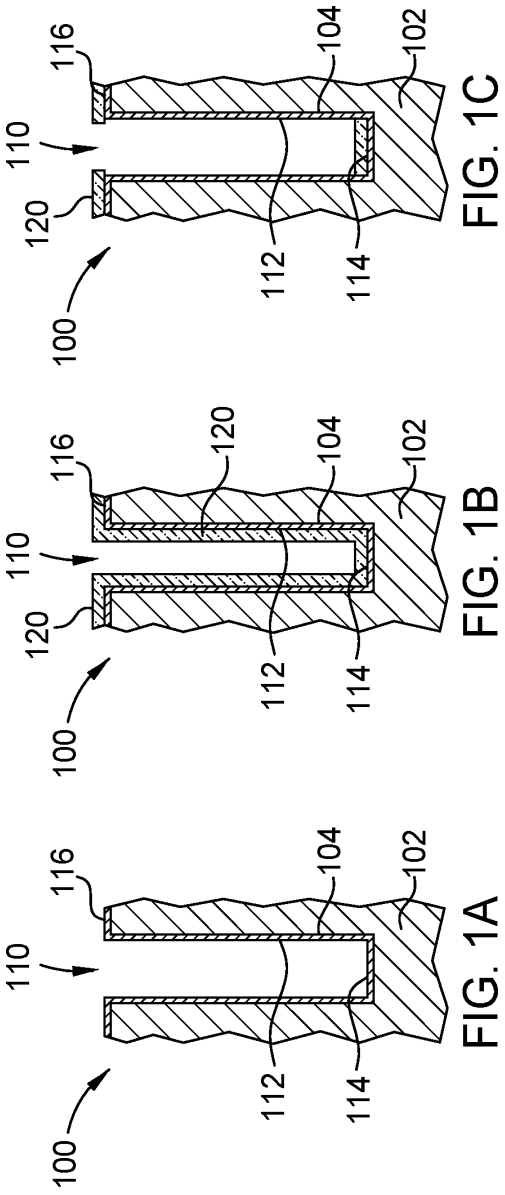


FIG. 1A

FIG. 1B

FIG. 1C

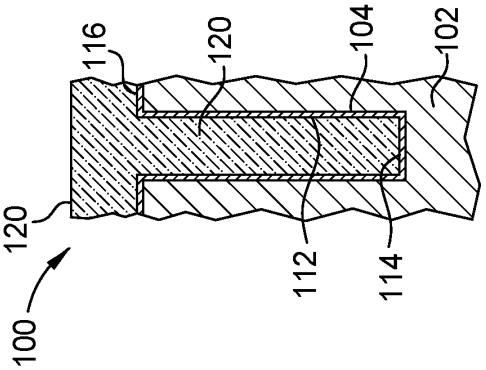


FIG. 1G

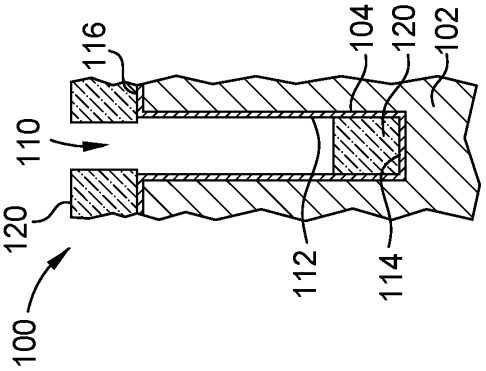


FIG. 1F

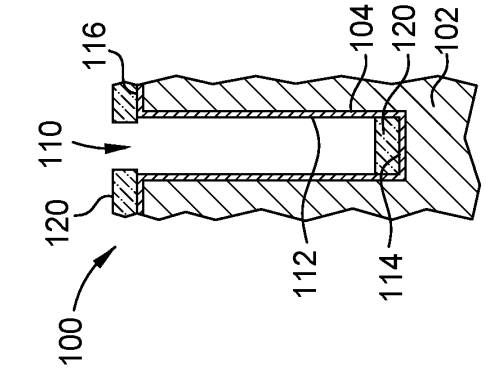


FIG. 1E

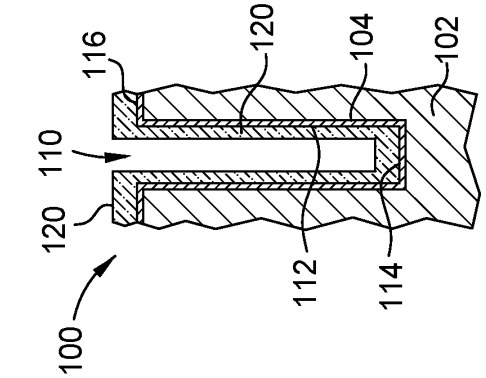


FIG. 1D

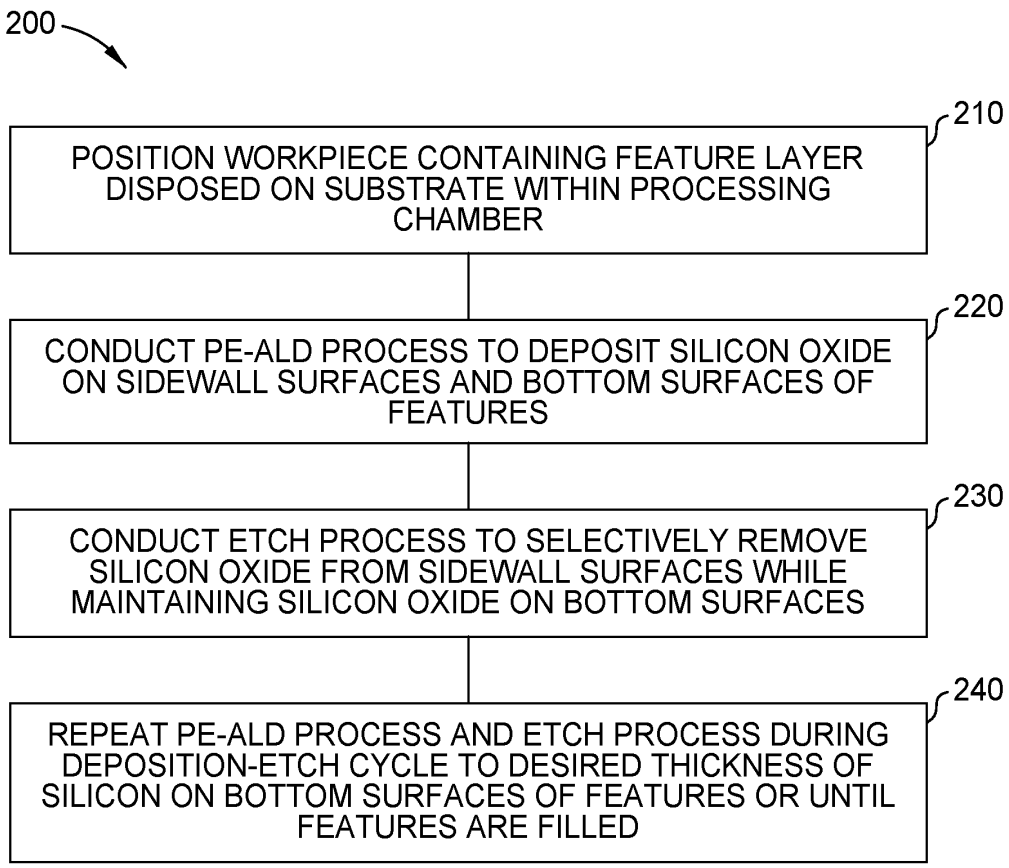

200
210
POSITION WORKPIECE CONTAINING FEATURE LAYER DISPOSED ON SUBSTRATE WITHIN PROCESSING CHAMBER
220
CONDUCT PE-ALD PROCESS TO DEPOSIT SILICON OXIDE ON SIDEWALL SURFACES AND BOTTOM SURFACES OF FEATURES
230
CONDUCT ETCH PROCESS TO SELECTIVELY REMOVE SILICON OXIDE FROM SIDEWALL SURFACES WHILE MAINTAINING SILICON OXIDE ON BOTTOM SURFACES
240
REPEAT PE-ALD PROCESS AND ETCH PROCESS DURING DEPOSITION-ETCH CYCLE TO DESIRED THICKNESS OF SILICON ON BOTTOM SURFACES OF FEATURES OR UNTIL FEATURES ARE FILLED

FIG. 2